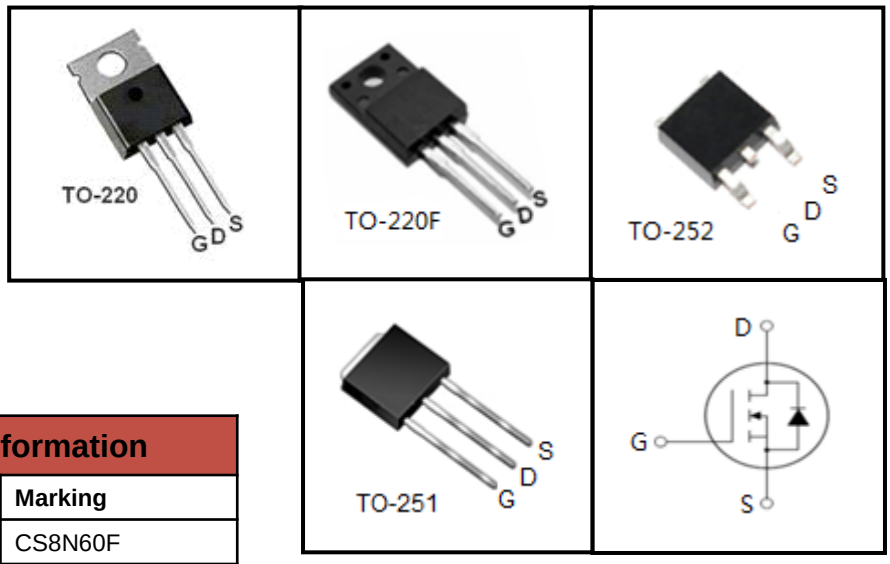
600V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information

Device	Package	Marking
CS8N60F	TO-220F	CS8N60F
CS8N60P	TO-220	CS8N60P
CS8N60U	TO-251	CS8N60U
CS8N60D	TO-252	CS8N60D
CS8N60F-B	TO-220F-B	CS8N60F-B

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter	Symbol	Value				Unit
		TO-220F	TO-220	TO-251	TO-252	
Drain-Source Voltage (V_{GS} = 0V)	V_{DSS}	600				V
Continuous Drain Current	I_D	8				A
Pulsed Drain Current (note1)	I_{DM}	32				A
Gate-Source Voltage	V_{GSS}	±30				V
Single Pulse Avalanche Energy (note2)	E_{AS}	217.8				mJ
Avalanche Current (note1)	I_{AR}	6.6				A
Repetitive Avalanche Energy (note1)	E_{AR}	130.6				mJ
Power Dissipation (T_C = 25ºC)	P_D	65	106			W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150				ºC

Thermal Resistance

Parameter	Symbol	Value				Unit
		TO-220F	TO-220	TO-251	TO-252	
Thermal Resistance, Junction-to-Case	R_{thJC}	1.95	1.17			ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	60			

Specifications T_J = 25ºC, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	600	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600V, V_{GS} = 0V, T_J = 25ºC	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	V_{GS} = 10V, I_D = 4A	--	0.85	1	Ω
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz	--	966	--	pF
Output Capacitance	C_{oss}		--	115.5	--	
Reverse Transfer Capacitance	C_{rss}		--	19.5	--	
Total Gate Charge	Q_g	V_{DD} = 480V, I_D = 8A, V_{GS} = 10V	--	35	--	nC
Gate-Source Charge	Q_{gs}		--	4.5	--	
Gate-Drain Charge	Q_{gd}		--	18.5	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 300V, I_D =8A, R_G = 25 Ω	--	38.5	--	ns
Turn-on Rise Time	t_r		--	28.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	153	--	
Turn-off Fall Time	t_f		--	43.6	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25 ºC	--	--	8	A
Pulsed Diode Forward Current	I_{SM}		--	--	32	
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 4A, V_{GS} = 0V	--	--	1.4	V
Reverse Recovery Time	t_{rr}	V_{GS} = 0V,I_S = 8A, di_F/dt =100A /μs	--	575.6	--	ns
Reverse Recovery Charge	Q_{rr}		--	1.96	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L=10mH, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25 ºC
3. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics (T_J = 25ºC)

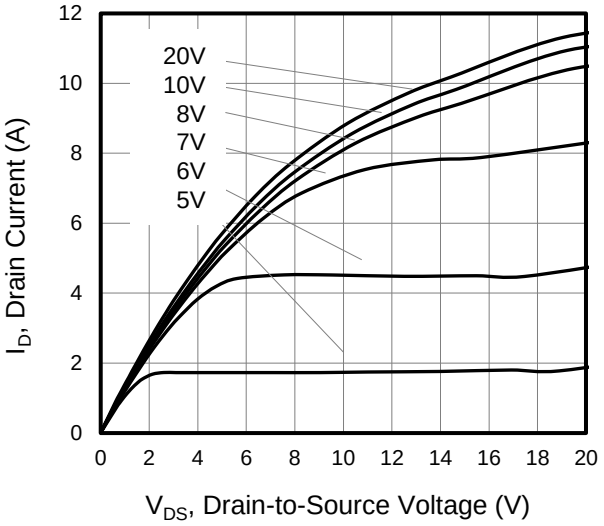


Figure 2. Body Diode Forward Voltage

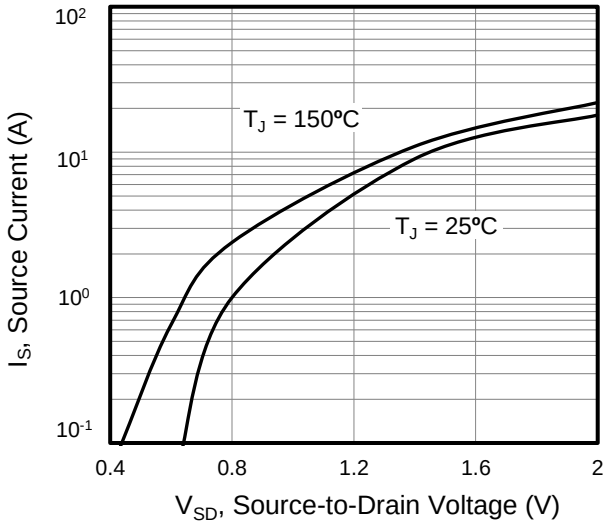


Figure 3. Drain Current vs. Temperature

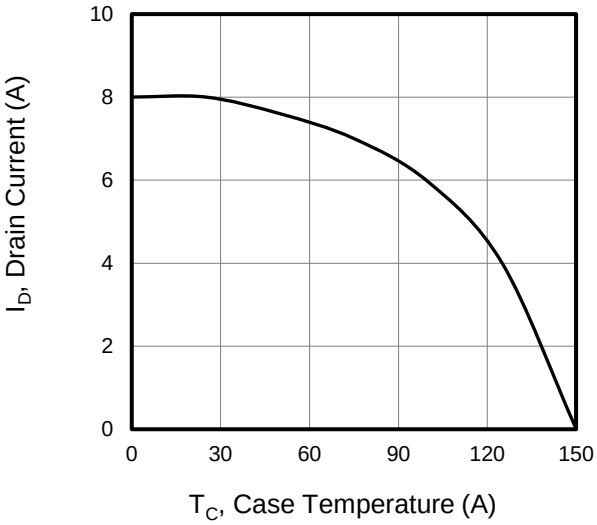


Figure 4. BV_{DSS} Variation vs. Temperature

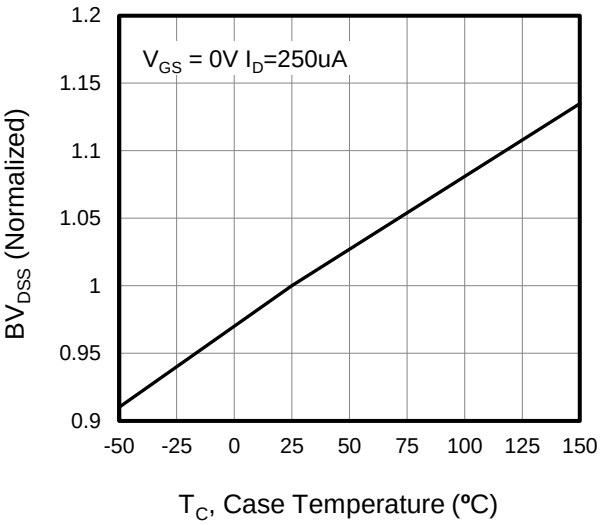


Figure 5. Transfer Characteristics

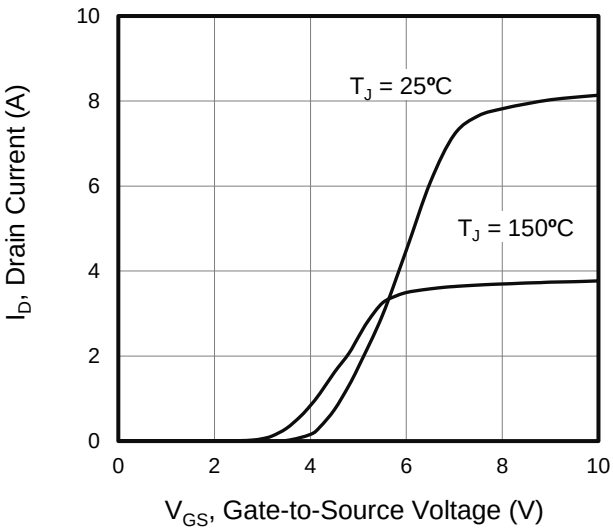
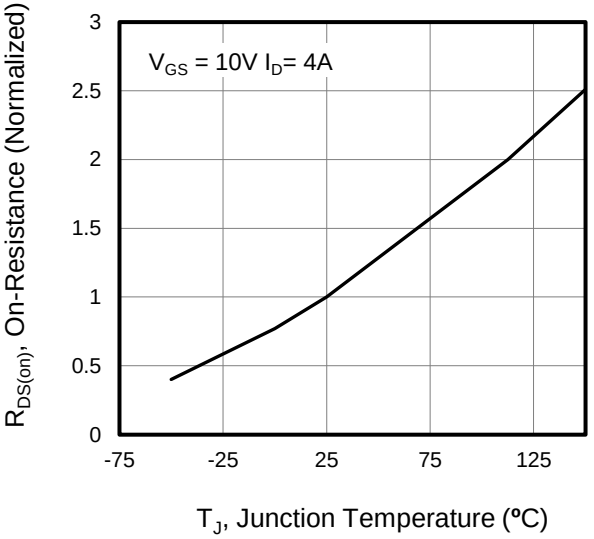


Figure 6. On-Resistance vs. Temperature



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Capacitance

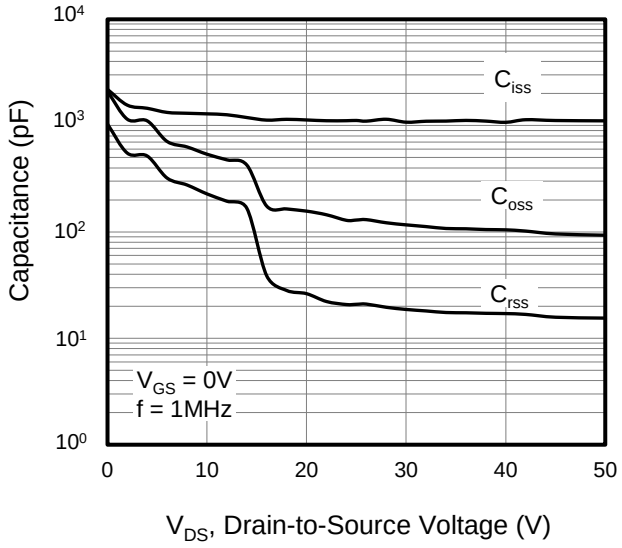


Figure 8. Gate Charge

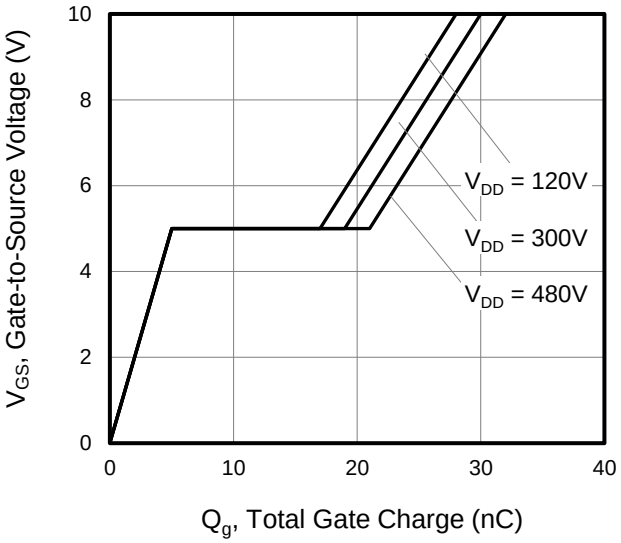


Figure 9. Transient Thermal Impedance

TO-251,TO-252,TO-220

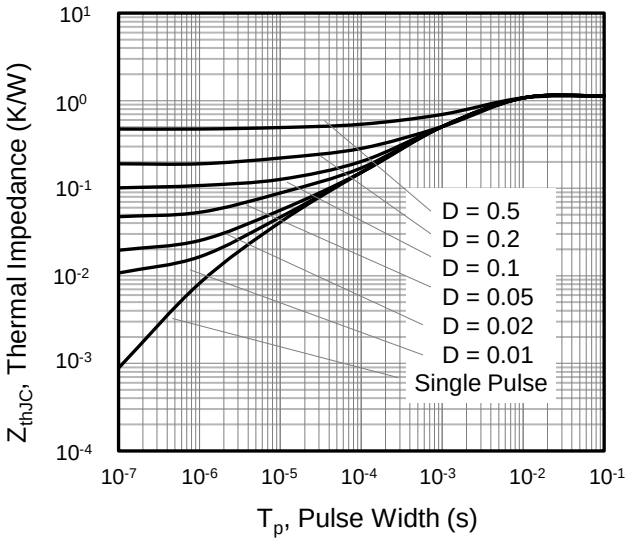


Figure 10. Transient Thermal Impedance

TO-220F

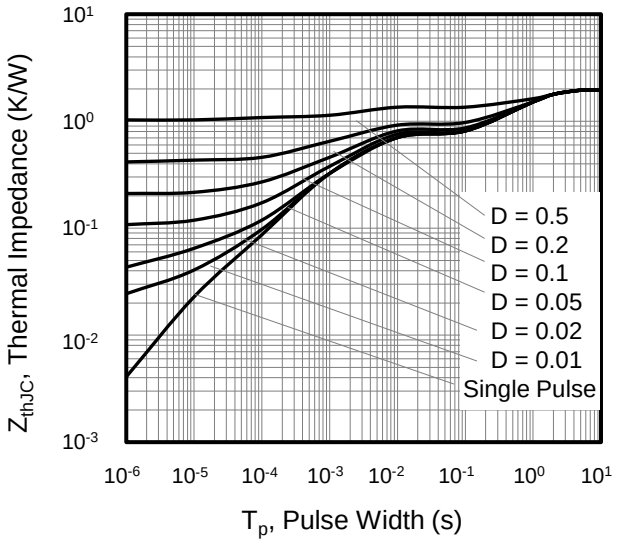


Figure A：Gate Charge Test Circuit and Waveform

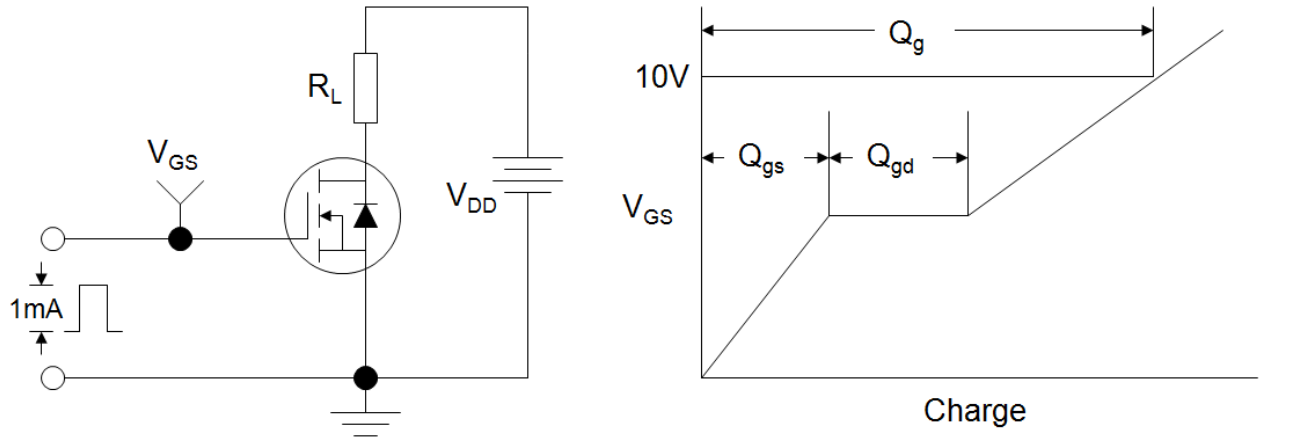


Figure B：Resistive Switching Test Circuit and Waveform

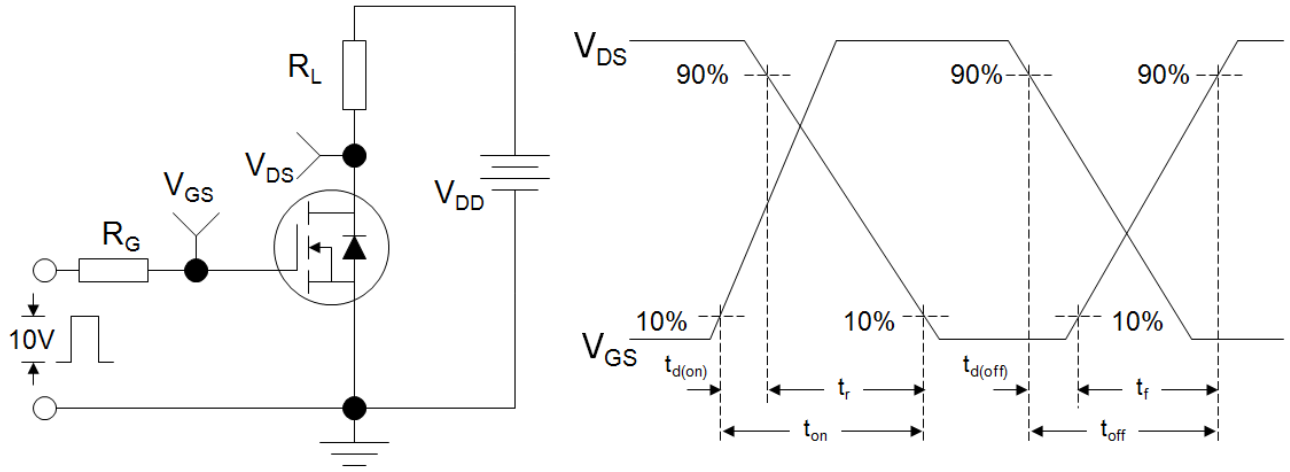
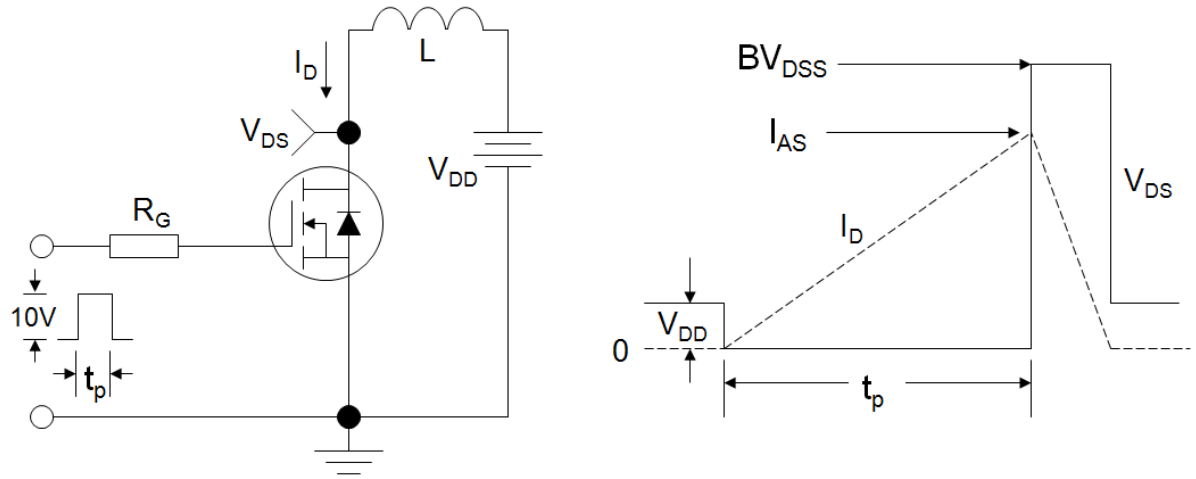
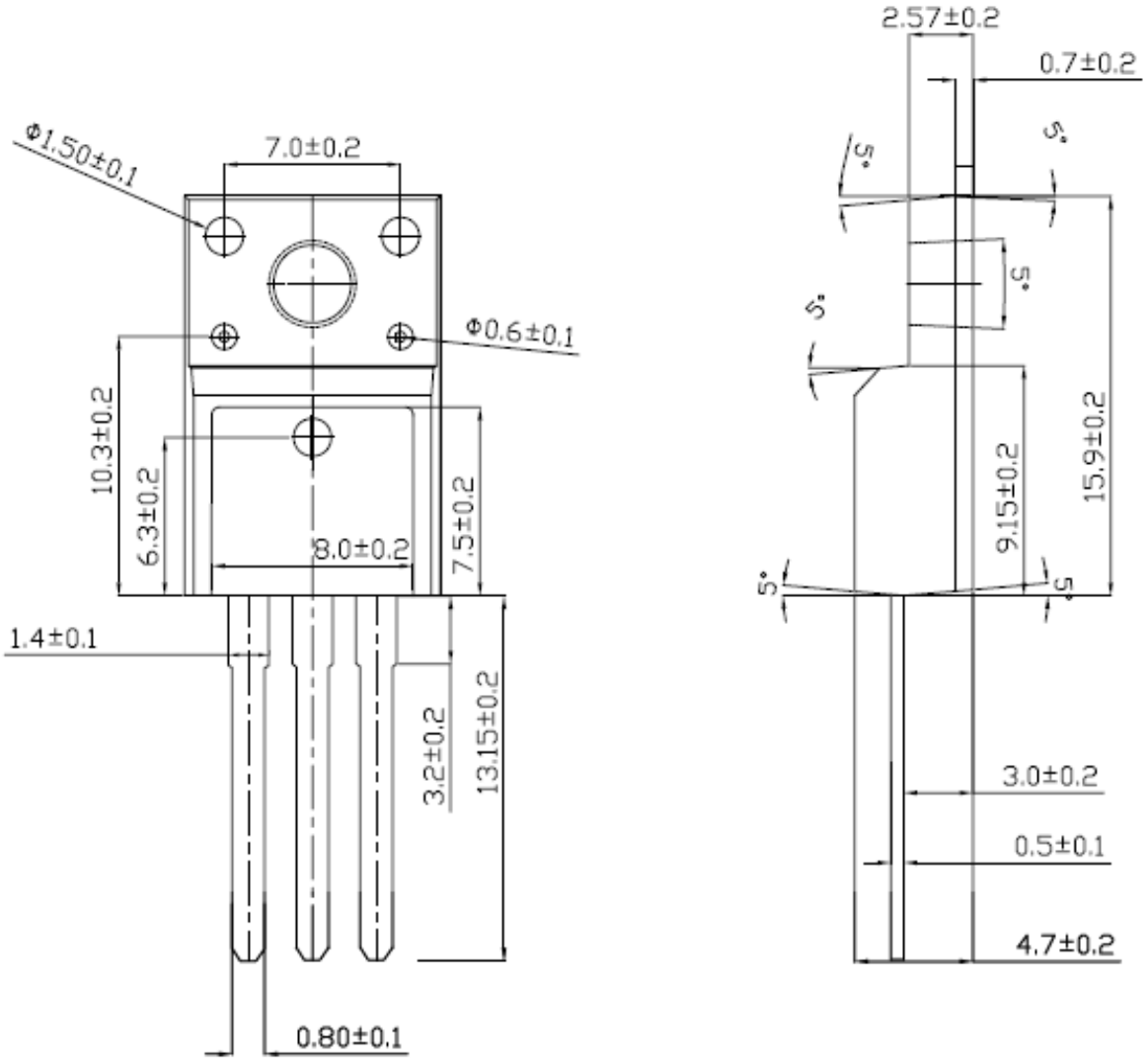


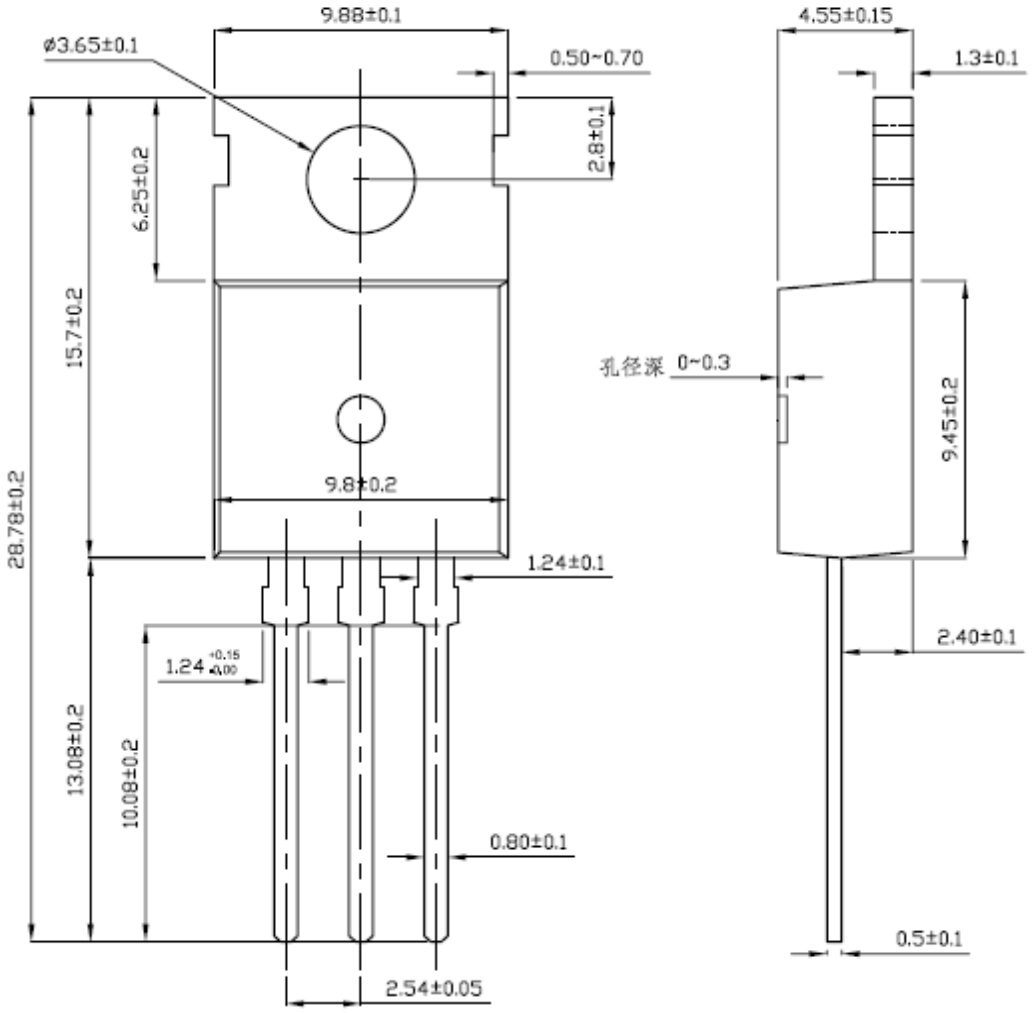
Figure C：Unclamped Inductive Switching Test Circuit and Waveform



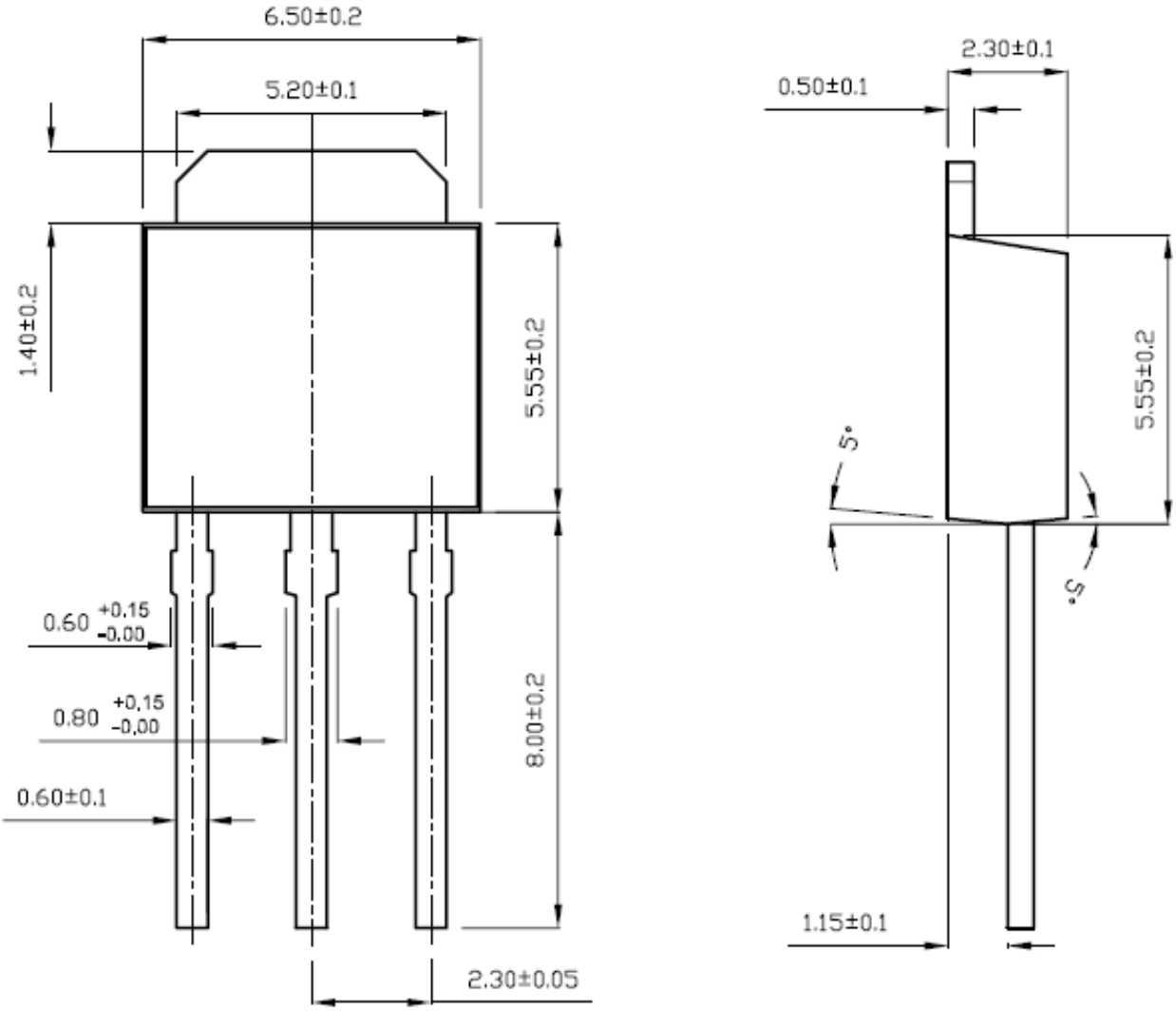
TO-220F


2.57±0.2
0.7±0.2
5°
5°
5°
5°
5°
5°
Φ1.50±0.1
7.0±0.2
Φ0.6±0.1
10.3±0.2
6.3±0.2
8.0±0.2
7.5±0.2
15.9±0.2
9.15±0.2
1.4±0.1
3.2±0.2
13.15±0.2
3.0±0.2
0.5±0.1
4.7±0.2
0.80±0.1

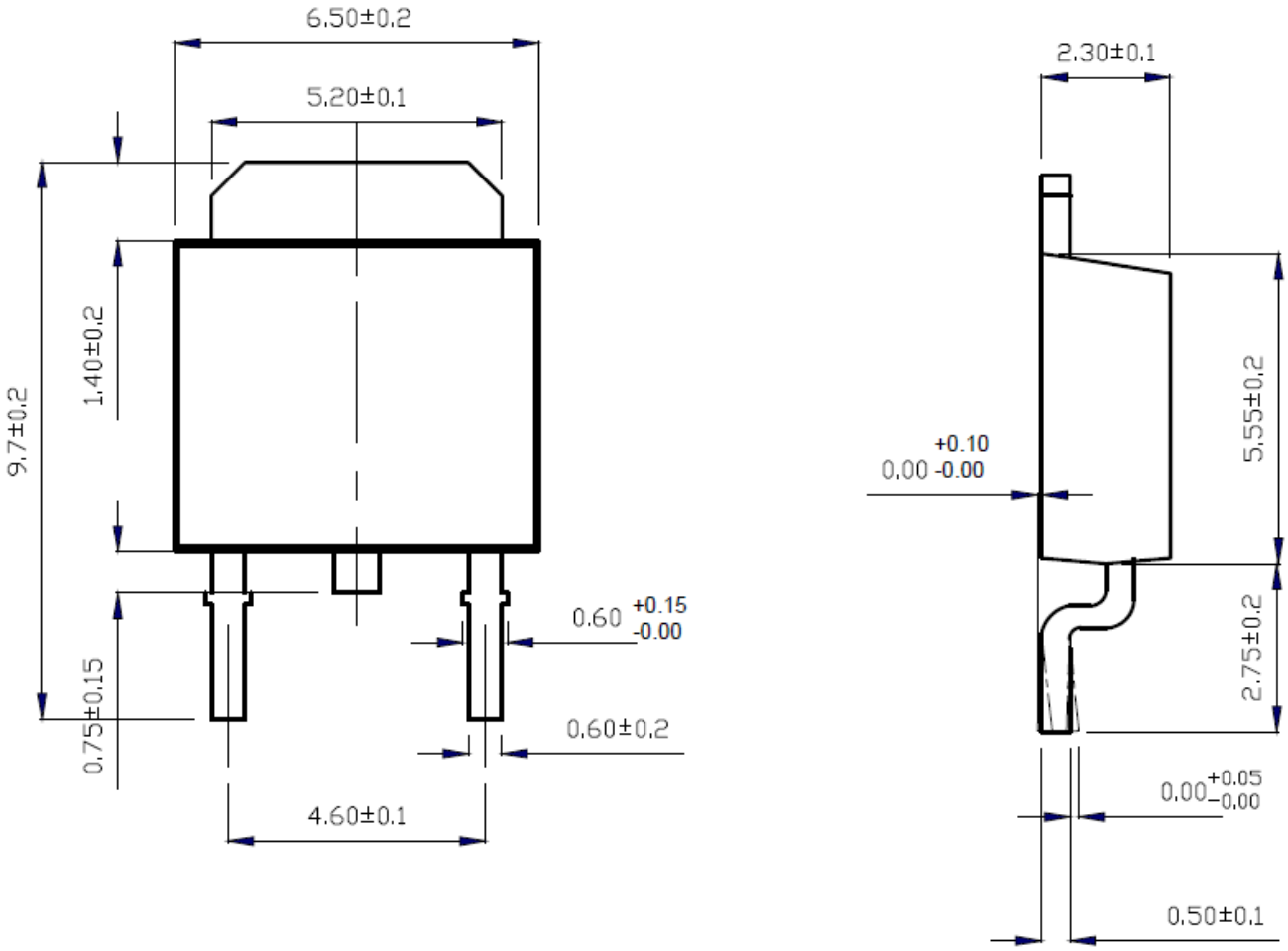
TO-220


9.88±0.1
ø3.65±0.1
0.50~0.70
2.8±0.1
6.25±0.2
15.7±0.2
28.78±0.2
9.8±0.2
1.24±0.1
1.24 +0.15 -0.00
13.08±0.2
10.08±0.2
0.80±0.1
2.54±0.05
4.55±0.15
1.3±0.1
孔径深 0~0.3
9.45±0.2
2.40±0.1
0.5±0.1

TO-251


6.50±0.2
5.20±0.1
1.40±0.2
5.55±0.2
0.60 +0.15 -0.00
0.80 +0.15 -0.00
0.60±0.1
8.00±0.2
2.30±0.05
2.30±0.1
0.50±0.1
5°
5°
5.55±0.2
1.15±0.1

TO-252


6.50±0.2
5.20±0.1
1.40±0.2
9.7±0.2
0.75±0.15
0.60 +0.15 -0.00
0.60±0.2
4.60±0.1
2.30±0.1
5.55±0.2
+0.10
0.00 -0.00
2.75±0.2
0.00 +0.05 -0.00
0.50±0.1

Disclaimer

All product specifications and data are subject to change without notice.

For documents and material available from this datasheet, Suzhou Convert does not warrant or assume any legal liability or responsibility for the accuracy, completeness of any product or technology disclosed hereunder.

No license, express or implied, by estoppels or otherwise, to any intellectual property rights is granted by this document or by any conduct of Suzhou Convert.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless. Customers using or selling Suzhou Convert products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Suzhou Convert for any damages arising or resulting from such use or sale.

Suzhou Convert disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Suzhou Convert's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

Suzhou Convert SemiConductor CO., Ltd. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

In the event that any or all Suzhou Convert products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Suzhou Convert believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by Convert Semiconductor ***manufacturer:***

Other Similar products are found below :

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3